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PATENT TRADEMARK OFFICE

Patent
Case No.: 57389US004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named Inventor: THEISS, STEVEN D

Application No.:

Group Art Unit: ---

Filed:

November 21, 2003

Examiner:

Unknown

Title:

METHOD OF MAKING TRANSISTORS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR §§ 1.56, 1.97, and 1.98, enclosed is a completed Form PTO-1449, citing references submitted for consideration by the Examiner. Copies of any cited foreign patents, non-patent literature, and unpublished US application documents are enclosed. Pursuant to the waiver in the Pre-OG Notice, dated July 11, 2003, copies of US patents and published US patent applications are no longer required and are not enclosed. It is respectfully requested that the Examiner initial and return the enclosed Form PTO-1449 to indicate that each reference has been considered.

Respectfully submitted,

Date

Nov 21, 2003

By:

Kent S. Kokko, Reg. No.: 33,931
Telephone No.: (651) 733-3597

Office of Intellectual Property Counsel
3M Innovative Properties Company
Facsimile No.: 651-736-3833

Substitute for form 1449A/PTO (modified) INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary) Page 1 of 2	Applicati n Number	---
	Filing Date	N v mber 20, 2003
	First Named Invent r	Theiss, Stev n D
	Art Unit	---
	Examiner Name	---
	Attorney Case Number	57389US004

U.S. Patent Documents					
Exam. Init.*	Cite No.	Document Number	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	(This field is not required Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Doc. Number-(Kind Code if Known) (Add Kind Code after patent No. when available)			
	A1	US- 2002/0195929 A1	12/26/2002	Haase et al.	
	A2	US- 2003/0100779 A1	05/29/2003	Vogel et al.	
	A3	US- 2003/0105365 A1	06/05/2003	Smith et al.	
	A4	US- 2003/0150384 A1	08/14/2003	Baude et al.	
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Foreign Patent Documents							
Exam. Init.*	Cite No.	Foreign Patent Document		Publication Date MM-DD-YYYY	(This field is not required)Name of Patentee or Applicant of Cited Document	(This field is not required Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Translation (Check if yes)
		Ctry. Code	Number-KindCode (if known)				
	B1	EP	0 762 806 A2	03/12/1997			
	B2	EP	1 003 221 A2	05/24/2000			
	B3	JP	2000-132762	05/12/2000			X
	B4	WO	00/10196	02/24/2000			
	B5						
	B6						
	B7						

*Examiner:	Date Considered:
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Substitute for form 1449A/PTO (modified) INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary) Page 2 of 2	Application Number	---
	Filing Date	November 20, 2003
	First Named Inventor	Theiss, Steven D
	Art Unit	---
	Examiner Name	---
	Attorney Case Number	57389US004

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS		
Exam. Init.*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published
	C1	S. M. SZE, Physics of Semiconductor Devices, (1981), pp. 438-442, 492-493, 2 nd Edition, John Wiley & Sons, New York
	C2	C. D. DIMITRAKOPOULOS et al., "Organic Thin-Film Transistors: A Review of Recent Advances", IBM J. Res. & Dev., (January 2001), pp.11-27, Vol. 45, No. 1
	C3	L. C. SANDER et al., "Polycyclic Aromatic Hydrocarbon Structure Index", NIST Special Publication 922 (December 1997)
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	C7	P. F. TIAN et al., "Precise, Scalable Shadow Mask Patterning, of Vacuum-Deposited Organic Light Emitting Devices", Journal of Vacuum Science & Technology A; Vacuum, Surfaces, and Films, (Sept/Oct 1999), 2 nd Series, Vol. 17, No. 5
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